

NTMFS5834NL, NVMFS5834NL

Power MOSFET

40 V, 75 A, 9.3 mΩ, Single N-Channel

Features

- Low $R_{DS(on)}$
- Low Capacitance
- Optimized Gate Charge
- NVMFS5834NLWF – Wettable Flanks Product
- NVMFS Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These Devices are Pb-Free and are RoHS Compliant

MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise stated)

Parameter			Symbol	Value	Unit
Drain-to-Source Voltage			V _{DSS}	40	V
Gate-to-Source Voltage			V _{GS}	±20	V
Continuous Drain Current R _{θJA} (Note 1)	Steady State	T _A = 25°C	I _D	14	A
		T _A = 100°C		12	
Power Dissipation R _{θJA} (Note 1)		T _A = 25°C	P _D	3.6	W
		T _A = 100°C		2.5	
Continuous Drain Current R _{θJC} (Note 1)		T _C = 25°C	I _D	75	A
		T _C = 100°C		63	
Power Dissipation R _{θJC} (Note 1)		T _C = 25°C	P _D	107	W
		T _C = 100°C		75	
Pulsed Drain Current	t _p = 10 μs		I _{DM}	276	A
Operating Junction and Storage Temperature			T _J , T _{STG}	-55 to +175	°C
Source Current (Body Diode)			I _S	75	A
Single Pulse Drain-to-Source Avalanche Energy (L = 0.1 mH)			EAS	48	mJ
			IAS	31	A
Lead Temperature for Soldering Purposes (1/8" from case for 10 s)			T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Case (Bottom) (Note 1)	$R_{\theta JC}$	1.4	$^\circ\text{C/W}$
Junction-to-Case (Top) (Note 1)	$R_{\theta JC}$	4.5	
Junction-to-Ambient Steady State (Note 1)	$R_{\theta JA}$	41	
Junction-to-Ambient Steady State (Note 2)	$R_{\theta JA}$	75	

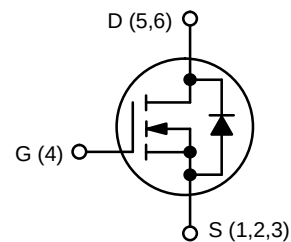
1. Surface-mounted on FR4 board using 1 sq-in pad (Cu area = 1.127 in sq [2 oz] including traces).
2. Surface-mounted on FR4 board using 0.155 in sq (100mm²) pad size.



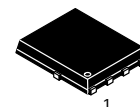
ON Semiconductor®

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$V_{(BR)DS}$	$R_{DS(ON)} \text{ MAX}$	$I_D \text{ MAX}$
40 V	9.3 mΩ @ 10 V	75 A
	13.6 mΩ @ 4.5 V	

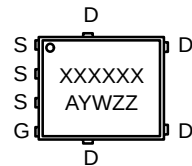


N-CHANNEL MOSFET



DFN5
(SO-8FL)
CASE 488AA
STYLE 1

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

NTMFS5834NL, NVMFS5834NL

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 250 μA	40			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			34.7		mV/°C
Zero Gate Voltage Drain Current	I _{DSS}	V _{GS} = 0 V, V _{DS} = 40 V	T _J = 25 °C		1.0	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA

ON CHARACTERISTICS (Note 3)

Gate Threshold Voltage	V _{GS(TH)}	V _{GS} = V _{DS} , I _D = 250 μA	1.0		3.0	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J			5.7		mV/°C
Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 20 A		7.1	9.3	mΩ
		V _{GS} = 4.5 V, I _D = 20 A		11.3	13.6	
Forward Transconductance	g _{FS}	V _{DS} = 5 V, I _D = 20 A		29		S

CHARGES, CAPACITANCES & GATE RESISTANCE

Input Capacitance	C _{ISS}	V _{GS} = 0 V, f = 1 MHz, V _{DS} = 20 V		1231		pF
Output Capacitance	C _{OSS}			198		
Reverse Transfer Capacitance	C _{RSS}			141		
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 10 V, V _{DS} = 20 V; I _D = 20 A		24		nC
Total Gate Charge	Q _{G(TOT)}	V _{GS} = 4.5 V, V _{DS} = 20 V; I _D = 20 A		12		
Threshold Gate Charge	Q _{G(TH)}			1.0		
Gate-to-Source Charge	Q _{GS}			4.2		
Gate-to-Drain Charge	Q _{GD}			6.3		
Plateau Voltage	V _{GP}			3.4		V
Gate Resistance	R _G			0.7		Ω

SWITCHING CHARACTERISTICS (Note 4)

Turn-On Delay Time	t _{d(ON)}	V _{GS} = 4.5 V, V _{DS} = 20 V, I _D = 20 A, R _G = 2.5 Ω		10		ns
Rise Time	t _r			56.4		
Turn-Off Delay Time	t _{d(OFF)}			17.4		
Fall Time	t _f			6.6		

DRAIN-SOURCE DIODE CHARACTERISTICS

Forward Diode Voltage	V _{SD}	V _{GS} = 0 V, I _S = 20 A	T _J = 25°C		0.84	1.2	V
			T _J = 125°C		0.72		
Reverse Recovery Time	t _{RR}	V _{GS} = 0 V, dI _S /dt = 100 A/μs, I _S = 20 A		18		ns	
Charge Time	t _a			10			
Discharge Time	t _b			8.0			
Reverse Recovery Charge	Q _{RR}			11		nC	

3. Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%.

4. Switching characteristics are independent of operating junction temperatures.

TYPICAL CHARACTERISTICS

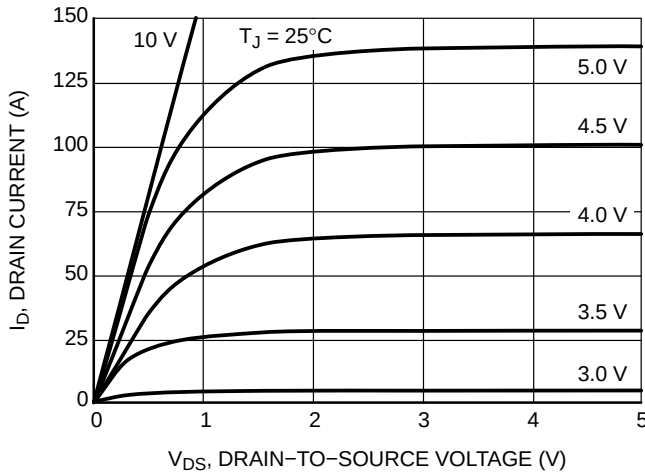


Figure 1. On-Region Characteristics

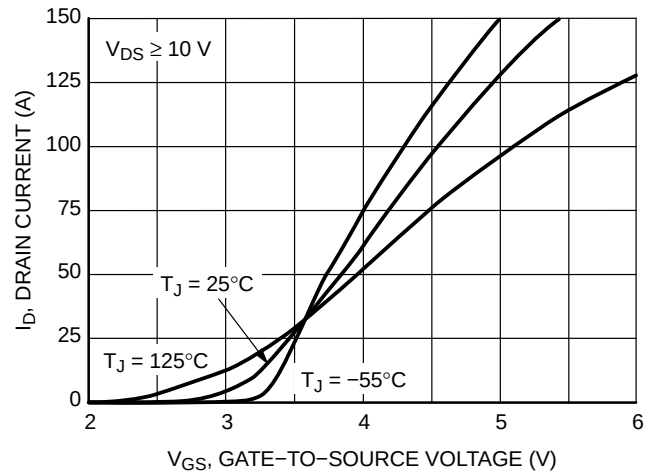


Figure 2. Transfer Characteristics

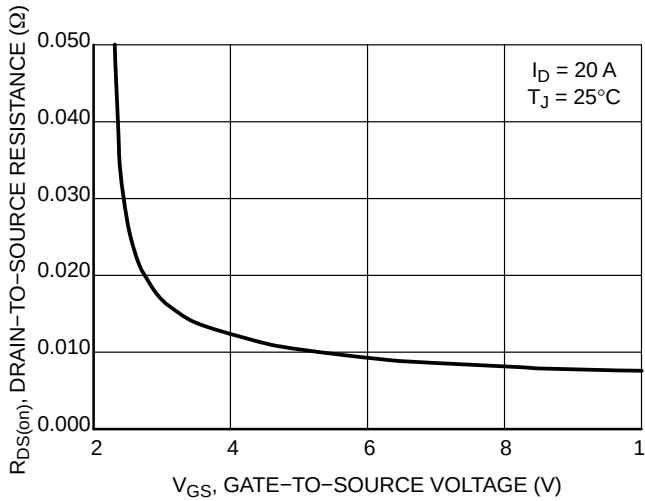


Figure 3. On-Resistance vs. Gate-to-Source Voltage

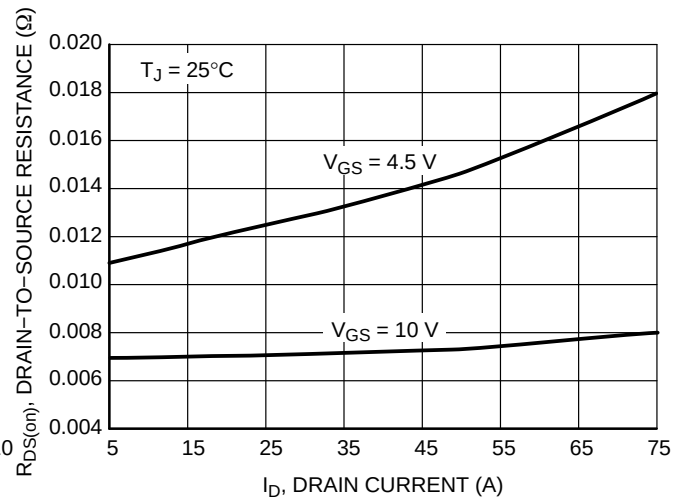


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

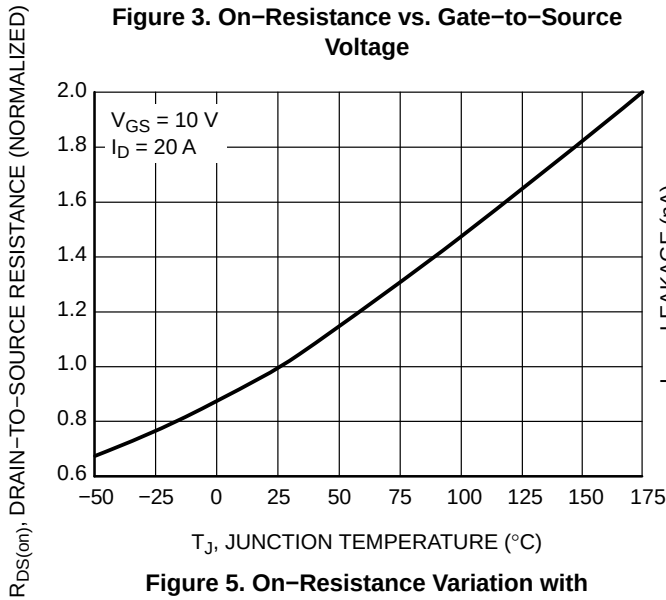


Figure 5. On-Resistance Variation with Temperature

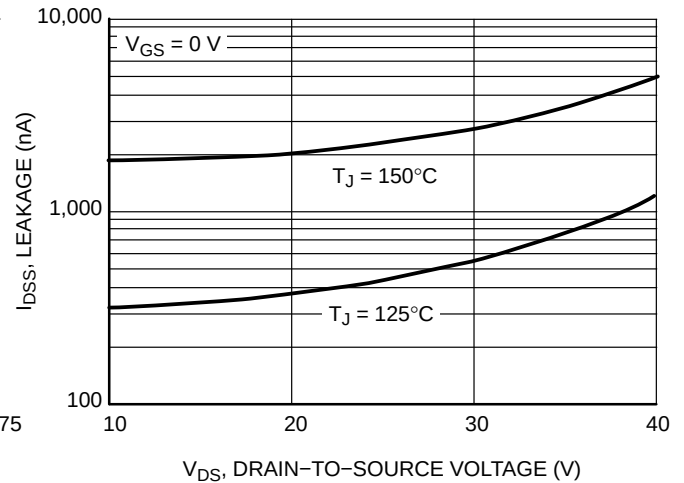


Figure 6. Drain-to-Source Leakage Current vs. Voltage

TYPICAL CHARACTERISTICS

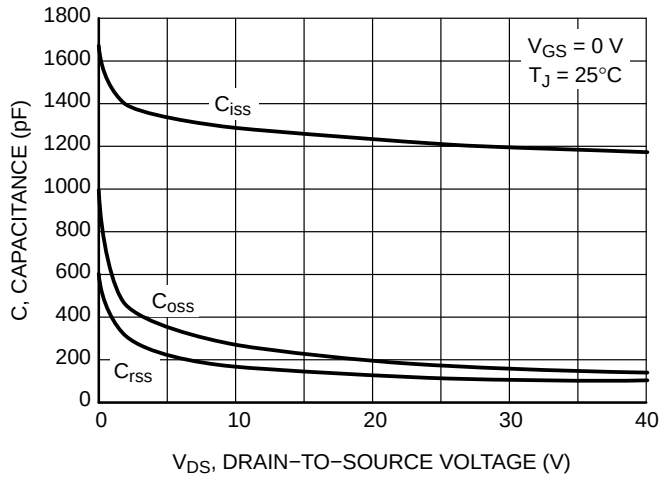


Figure 7. Capacitance Variation

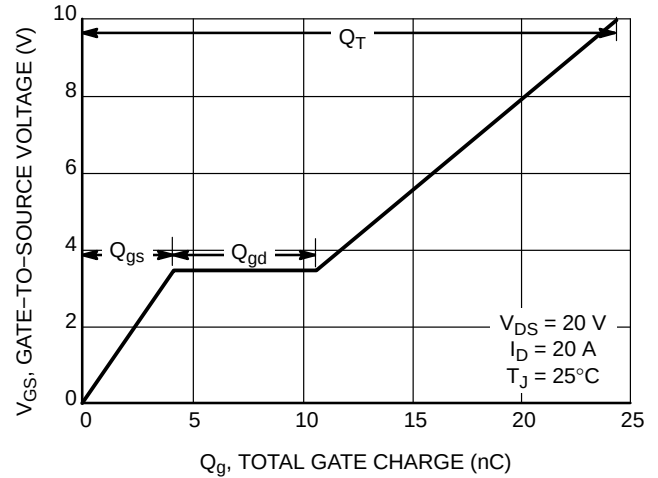


Figure 8. Gate-to-Source Voltage vs. Total Charge

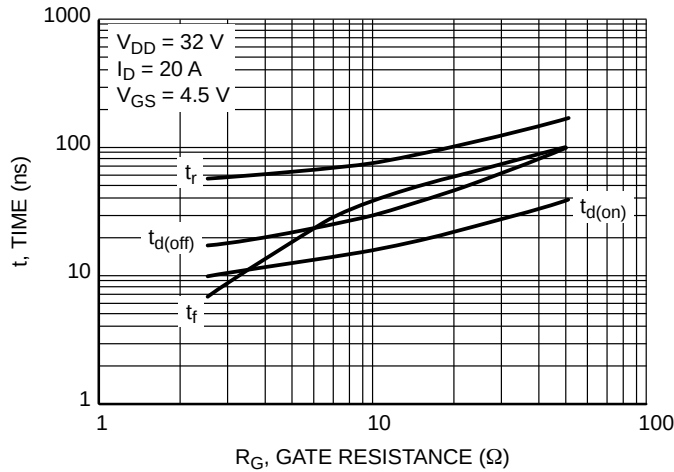


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

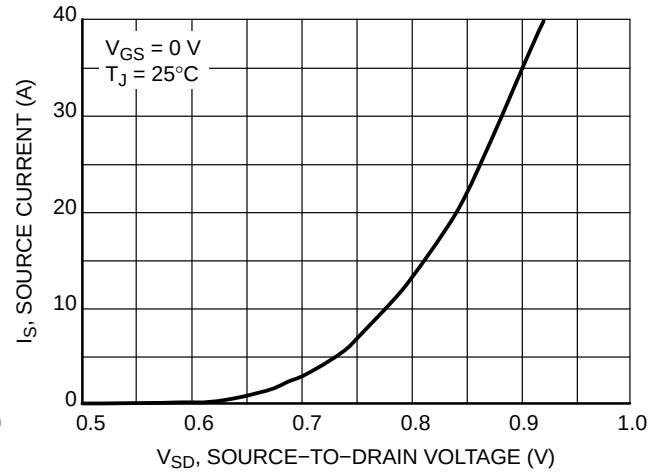


Figure 10. Diode Forward Voltage vs. Current

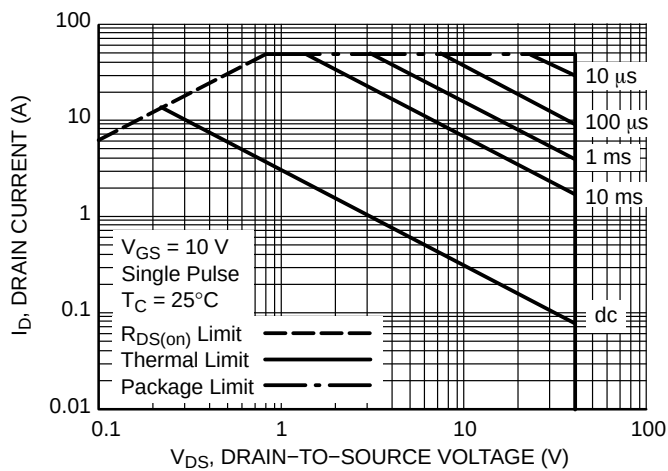


Figure 11. Maximum Rated Forward Biased Safe Operating Area

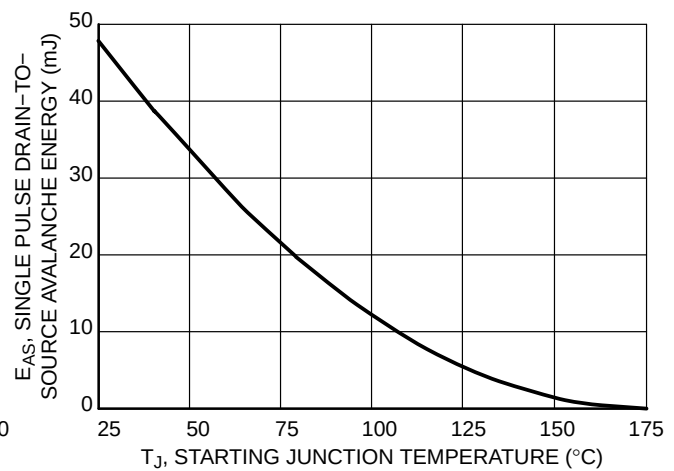


Figure 12. Maximum Avalanche Energy vs. Starting Junction Temperature

NTMFS5834NL, NVMFS5834NL

TYPICAL CHARACTERISTICS

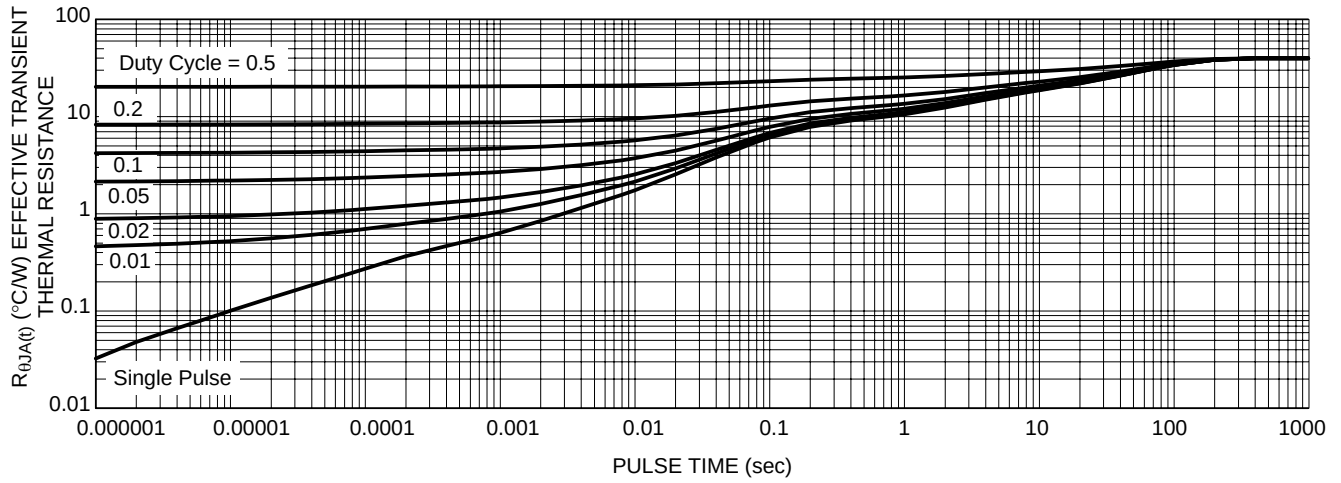
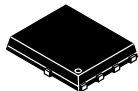


Figure 13. Thermal Response

DEVICE ORDERING INFORMATION

Device	Marking	Package	Shipping [†]
NTMFS5834NLT1G	5834L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5834NLT1G	V5834L	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5834NLWFT1G	5834LW	DFN5 (Pb-Free)	1500 / Tape & Reel
NVMFS5834NLT3G	V5834L	DFN5 (Pb-Free)	5000 / Tape & Reel
NVMFS5834NLWFT3G	5834LW	DFN5 (Pb-Free)	5000 / Tape & Reel

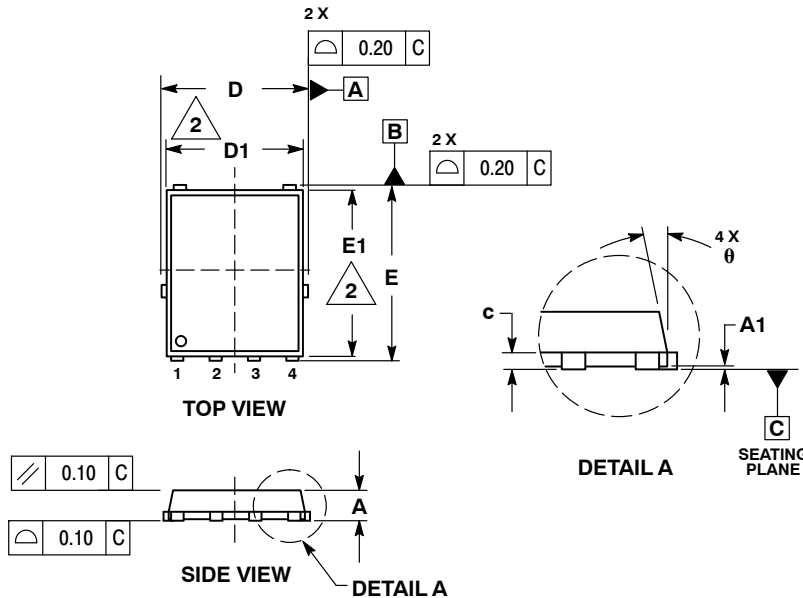
[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.



SCALE 2:1

DFN5 5x6, 1.27P
(SO-8FL)
CASE 488AA
ISSUE N

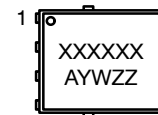
DATE 25 JUN 2018



NOTES:

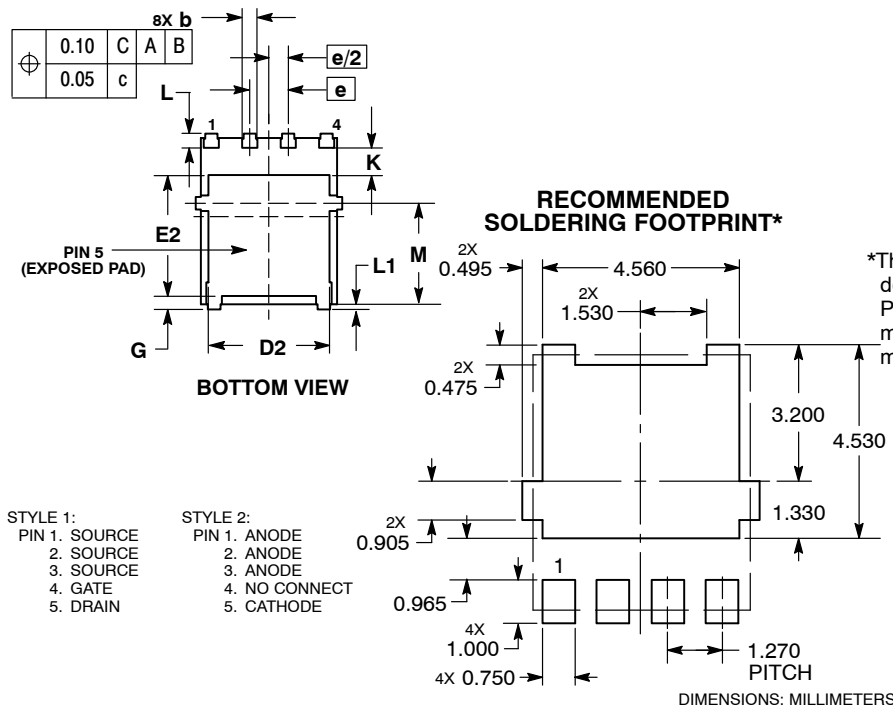
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETER.
3. DIMENSION D1 AND E1 DO NOT INCLUDE MOLD FLASH PROTRUSIONS OR GATE BURRS.

DIM	MILLIMETERS		
	MIN	NOM	MAX
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.70	4.90	5.10
D2	3.80	4.00	4.20
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.45	3.65	3.85
e	1.27 BSC		
G	0.51	0.575	0.71
K	1.20	1.35	1.50
L	0.51	0.575	0.71
L1	0.125 REF		
M	3.00	3.40	3.80
theta	0°	---	12°

GENERIC
MARKING DIAGRAM*


XXXXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceability

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



*For additional information on our Pb-Free strategy and soldering details, please download the onsemi Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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